

SIC SCHOTTKY DIODE TYPE 2×25A

Features

- High surge current capable
- Zero reverse recoveryZero forward recovery
- Isolation type package
- Temperature independent switching behavior
- V_{DC} 1200 V • I_{F (To<135°C)} 2×25 A

Benefits

- Unipolar rectifier
- Smaller heat sink
- Higher efficiency

Applications

- · Motor drives
- Switch mode power supplies
- Ev chargers
- Solar inverters
- Welding equipment
- Power factor correction
- Diode snubber
- Automotive
- · induction heating

Maximum Ratings

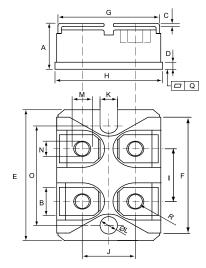
Operating Junction Temperature : -55°C to +175°C

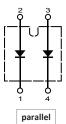
Storage Temperature : -55°C to +175°C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
CSRI2×25-120P3B	1200V	1200V

Maximum Rating	Symbol	Conditions	Value	Unit	
Continuous forward current (per diode)	I _F	T _C =135 °C	25		
Surge non-repetitive forward current	I _{ESM}	T_C =25 °C, t_p =8.3 ms	200		
sine halfwave (per diode)	T GIVI	T _C =150 °C, t _p =8.3 ms	125	Α	
Non-repetitive peak forward current	I _{F,max}	T_{C} =25 °C, t_{p} =10 μ s	800		
(per diode)		T_{C} =150 °C, t_{p} =10 μ s	500		
Repetitive peak reverse voltage	V_{RRM}	T _J =25 °C	1200	٧	
Isolation voltage (between All Terminals and Baseplate)	V _{iso}	50/60 Hz, t=1min I _{ISOL} ≤ 1mA	2500	٧	
Mounting torque	Md	To heatsink	1.3	Nm	
mounting torque		To terminal	1.1		







DIMENSIONS						
	INCH	IES	Mi	M		
	MIN	MAX	MIN	MAX		
Α	0.460	0.483	11.68	12.28		
В	0.307	0.323	7.80	8.20		
С	0.030	0.033	0.75	0.85		
D	0.071	0.081	1.80	2.05		
Е	1.488	1.504	37.80	38.20		
F	1.248	1.260	31.70	32.00		
G	0.917	0.957	23.30	24.30		
Н	0.996	1.008	25.30	25.60		
I	0.579	0.602	14.70	15.30		
J	0.492	0.516 12.50		13.10		
K	0.161	0.169 4.10		4.30		
L	0.161	0.169 4.10		4.30		
М	0.181	0.197	4.60	5.00		
N	0.165	0.181	4.20	4.60		
0	1.181	1.197	30.00	30.40		
Q	-0.002	0.004	-0.05	0.10		
R	R M4*8					



Electrical Characteristics, at T_j=25 °C, unless otherwise specified. (per diode)

Static Characteristics	Symbol	Conditions	Values			
			min.	typ.	max.	Unit
DC blocking voltage	V_{DC}		1,200	-	-	V
Diode forward voltage	V _F	I _F =25A, T _J =25 °C	-	1.5	1.7	V
		I _F =25A, T _J =175 °C	-	2.3	2.8	
Reverse current	I _R	V _R =1,200V, T _J =25 °C	-	5	25	- μΑ
		V _R =1,200V, T _J =175 °C	-	50	200	

AC Characteristics (per diode)

Static Characteristics	Symbol	Conditions	Values			
			min.	typ.	max.	Unit
Total capacitive charge	Q _{rr}	VR =800V	-	121	-	nC
Total capacitance	С	V _R =1V, f=1 MHz T _J =25 °C	-	1,360	-	- pF
		V _R =800V, f=1 MHz T _J =25 °C	-	85	-	

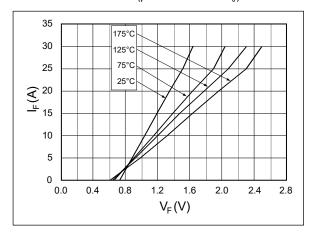
Thermal Characteristics (per diode)

Statio Characteristics	Cumbal	Values		
Static Characteristics	Symbol	typ.	Unit	
Thermal resistance from junction to case	$R_{ heta JC}$	0.56	°C/W	

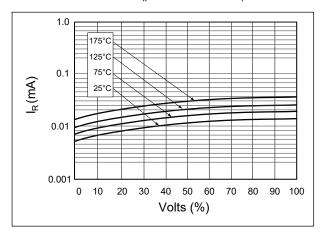


Typical Performance

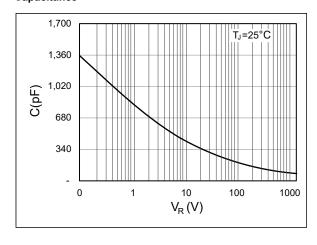
Forward Characteristics (parameterized on T_J)



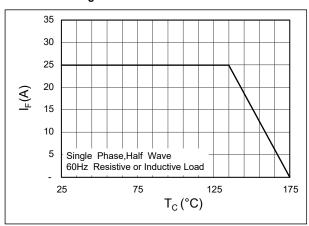
Reverse Characteristics (parameterized on TJ)



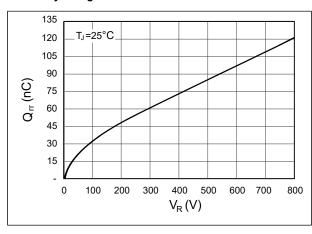
Capacitance



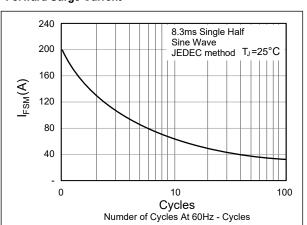
Current Derating



Recovery Charge



Forward Surge Current





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